NTSV20120CT

Very Low Forward Voltage Trench-based Schottky Rectifier

Exceptionally Low V_F = 0.557 V at I_F = 5 A

Features

- Fine Lithography Trench−based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- Low Thermal Resistance
- High Surge Capability
- This Device is Pb−Free, Halogen Free/BFR Free and is RoHS Compliant

Typical Applications

- Switching Power Supplies including Notebook/Netbook Adapters, ATX and Flat Panel Display
- High Frequency and DC−DC Converters
- Freewheeling and OR−ing Diodes
- Reverse Battery Protection
- Instrumentation

Mechanical Characteristics

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94−0 @ 0.125 in
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Maximum for 10 sec

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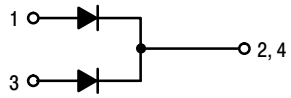
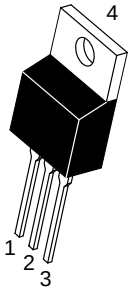
http://onsemi.com

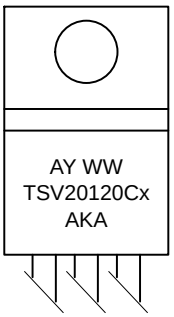
PIN CONNECTIONS





TO−220
CASE 221A
STYLE 6

MARKING DIAGRAM



A	= Assembly Location
Y	= Year
WW	= Work Week
AKA	= Polarity Designator
x	= G or H
G	= Pb−Free Package
H	= Halide−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NTSV20120CTG	TO−220 (Pb−Free)	50 Units / Rail

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	120	V
Average Rectified Forward Current (Rated V_R, T_C = 115°C) Per Device Per Diode	$I_{F(AV)}$	 20 10	A
Peak Repetitive Forward Current (Rated V_R, Square Wave, 20 kHz, T_C = 110°C) Per Device Per Diode	I_{FRM}	 40 20	A
Non-repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	 100	A
Operating Junction Temperature	T_J	−40 to +150	°C
Storage Temperature	T_{stg}	−40 to +150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	10,000	V/μs

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Maximum Thermal Resistance Junction−to−Case Junction−to−Ambient	 $R_{\theta JC}$ $R_{\theta JA}$	 2.0 70	°C/W

ELECTRICAL CHARACTERISTICS (Per Leg unless otherwise noted)

Rating	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 1) (I_F = 5 A, T_J = 25°C) (I_F = 10 A, T_J = 25°C) (I_F = 5 A, T_J = 125°C) (I_F = 10 A, T_J = 125°C)	v_F	 0.654 0.874 0.557 0.650	 – 1.12 – 0.86	V
Maximum Instantaneous Reverse Current (Note 1) (V_R = 90 V, T_J = 25°C) (V_R = 90 V, T_J = 125°C) (Rated dc Voltage, T_J = 25°C) (Rated dc Voltage, T_J = 125°C)	I_R	 5.8 4.9 16.1 8.9	 700 100	 μA mA μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%

TYPICAL CHARACTERISTICS

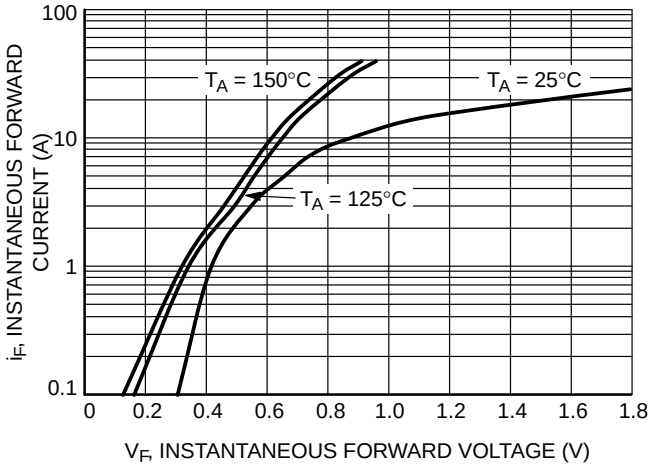


Figure 1. Typical Instantaneous Forward Characteristics

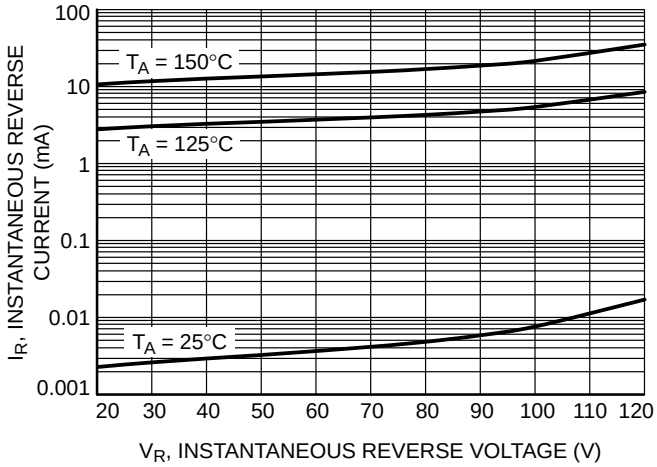


Figure 2. Typical Reverse Characteristics

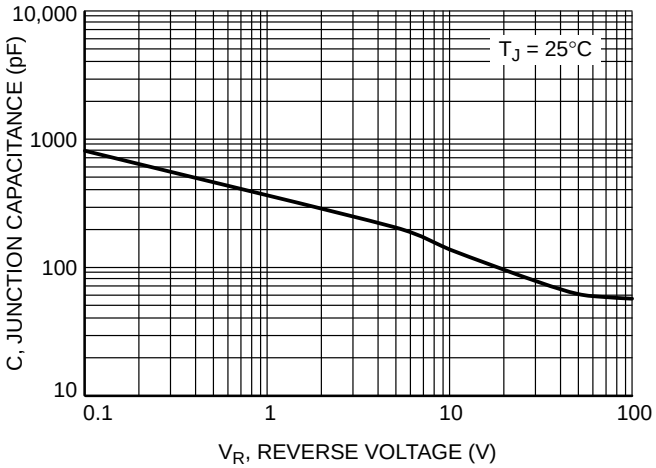


Figure 3. Typical Junction Capacitance

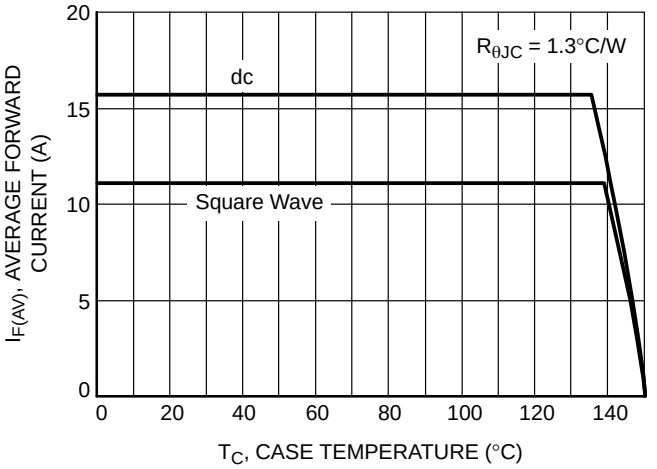


Figure 4. Current Derating per Leg

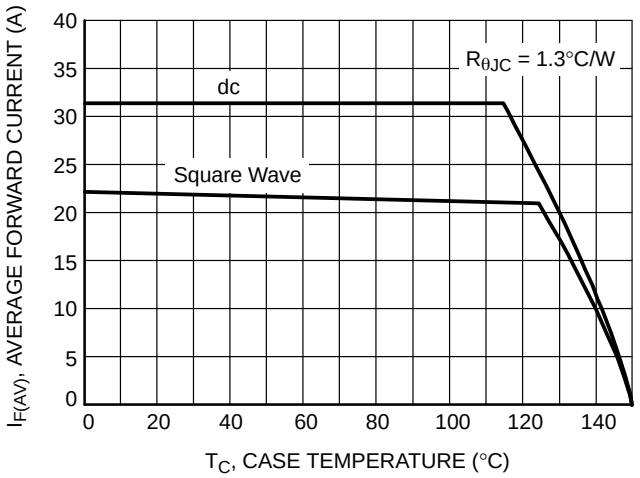


Figure 5. Current Derating

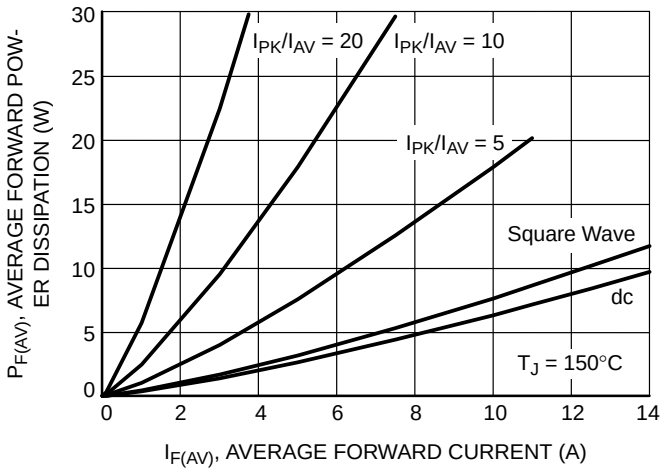


Figure 6. Forward Power Dissipation

TYPICAL CHARACTERISTICS

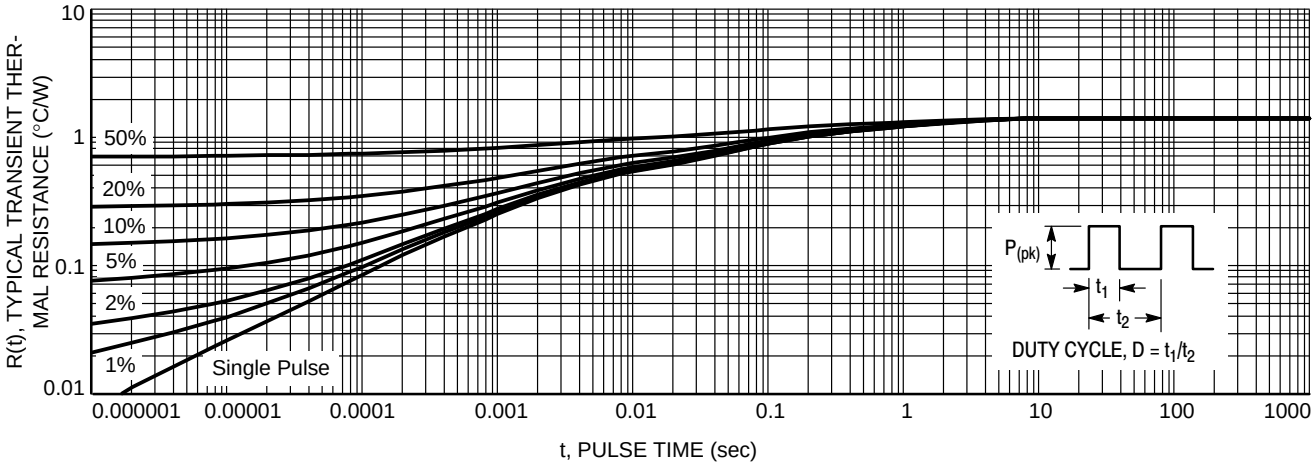


Figure 7. Typical Transient Thermal Response

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

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